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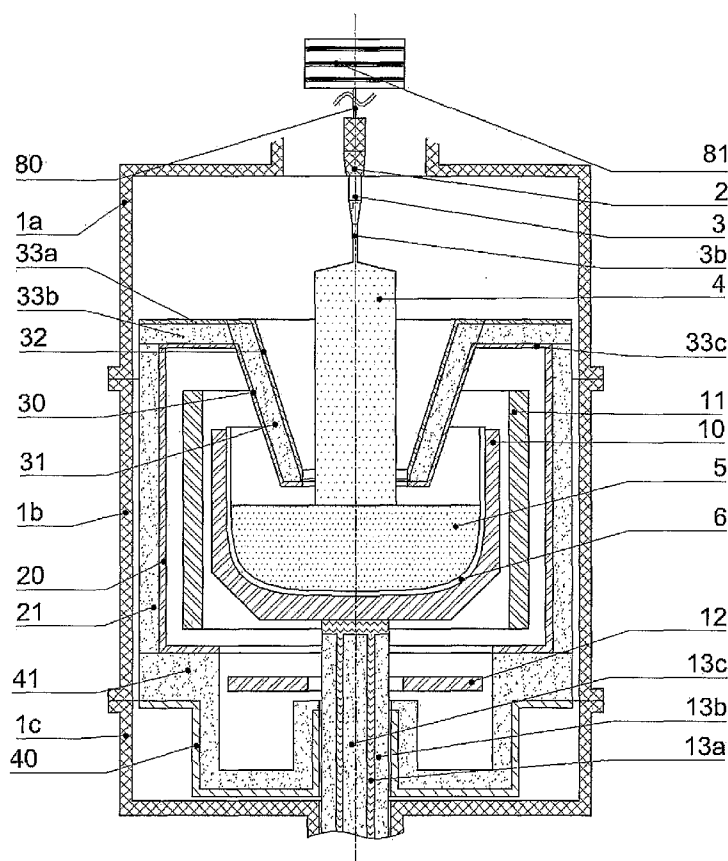
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(54) Title: CRYSTAL MANUFACTURING



(57) Abstract: An implementation of a Czochralski-type crystal growth has been shown and embodied. More particularly, a furnace with suitable insulation and flow arrangement is shown to improve the cost-efficiency of production of crystals. That is achieved by the shown new hot-zone structure, gas flows and the growth process which can decrease the power consumption, increase the lifetime of hot-zone parts and improve the productivity, e.g., by giving means for opening the hot-zone and easily adapting the hot-zone to a new crystal diameter.



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